I hereby certify that this correspondence and sing deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to "Commissioner for Patents, Washington, DC 20231" on

Atty Dr. No. ARC920010125US1 R&A No. 5075-0034 PATENT

Date Signature 20231 on

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Hiroshi ITO

Serial No.: 10/091,373

Filing Date: March 4, 2002

Group Art Unit: 1752

Examiner: Unassigned

Title: COPOLYMER FOR USE IN CHEMICAL AMPLIFICATION RESISTS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents Washington, DC 20231

Sir:

This is an Information Disclosure Statement submitted for the Examiner's consideration. Applicants respectfully request that the Examiner review and make of record the references identified below.

A PTO-1449 form listing the references accompanies this paper. Applicants would appreciate the Examiner's initialing and returning the form to indicate that the references have been reviewed and made of record. The references are as follows:

	U.S. PATENT DOCUMENTS	
Document No.	Issue Date or Publication Date	Name of Patentee or Applicant
5,344,742	9/6/94	Sinta et al.
6,087,064	7/11/00	Lin et al.

	NONPATENT DOCUMENTS
1 recritiology 13(4):03/-	77 nm Resist Materials: A Progress Report," Journal of Photopolymer Science and 664.
Technology and Froces	sign and Synthesis of New Photoresist Materials for ArF Lithography," Advances in Resist sing XVII, Proceeding of SPIE 3999:54-61.
Ito et al. (1981), "Meth 24(2):991.	yl a-Trifluoromethylacrylate, an E-Beam and UV Resist," IBM Technical Disclosure Bulletin
Copolymenzamon of Ti	nerization of Methyul α-(Trifluoromethyl)acrylate and α-(Trifluoromethyl)Acrylonitrile and hese Monomers with Methyl Methacrylate," <i>Macromolecules</i> 15(3):915-920.
10 (1984), Radical Re 17(10):2204-2205.	activity and Q-e Values of Methyl α-(Trifluoromethyl)acrylate," Macromolecules
Ito et al. (1987), "Anior Polymerization, Elsevie	nic Polymerization of α-(Trifluoromethyl)acrylate," Recent Advances in Anionic

NONPATENT DOCUMENTS

Ito et al. (2001), "Novel Fluoropolymers for Use in 157 nm Lithography," Journal of Photopolymer Science and Technology 14(4):583-593.

Ito et al. (2001), "Polymer Design for 157 nm Chmically Amplified Resists," Advances in Resist Technology and Processing XVIII, Proceedings of SPIE 4345:273-284.

Kunz et al. (1999), "Outlook for 157 nm Resist Design," Proceedings of SPIE 3678:13-23.

Schmidt et al. (1962), "Ozonisierung Cyclischer Enolather," Liebigs Ann. Chem. Bd. 656:97-102.

Willson et al. (1983), "Poly(Methyl α-Trifluoromethylacrylate) as a Positive Electron Beam Resist," *Polymer Engineering and Science* 23(18):1000-1003.

This Information Disclosure Statement is not intended as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that any of the above references constitutes prior art to the present application within the meaning of 35 USC § 102.

As applicants have not yet received a first Action on the merits, no fee is required for filing this Information Disclosure Statement. If, however, the PTO finds that for some reason a fee is found to be necessary, our Deposit Account No. 18-0580 may be charged therefor. A duplicate copy of this paper is enclosed.

Respectfully submitted,

By:

Dianne E. Reed

Registration No. 31,292

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	Application Number	10/091,373	
	Filing Date	March 4, 2002	
	First Named Inventor	Hiroshi ITO	
	Art Unit	1752	
i	Examiner Name	Unassigned	
	Attorney Docket Number	ARC920010125US1	

- F			U.S. PATENT I	OCUMENTS			
Examiner Initials*	Cite No.	Document No.	Issue Date or Publication Date	Name of Patentee or Applicant of Cited Document	Class	Subclass	Filing Date
	AA	5,344,742	9/6/94	Sinta et al.	 	 	if Appropriate
	AB	6,087,064	7/11/00	Lin et al.	 		

F	- At-	OTHER DOCUMENTS — NONPATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.	journal, serial, symposium, catalog, etc.), date, page(s), volume issue number(s), publisher, site of the item (book, magazine,	T
	ĄC	Chiba et al. (2000), "157 nm Resist Materials: A Progress Report," Journal of Photopolymer Science and Technology 13(4):657-664.	+
1	AD	Choi et al. (2000), "Design and Synthesis of New Photoresist Materials for ArF Lithography," Advances in Resist Technology and Processing XVII, Proceeding of SPIE 3999:54-61.	\vdash
-	. AE	Ito et al. (1981), "Methyl α-Trifluoromethylacrylate, an E-Beam and UV Resist," IBM Technical Disclosure Bulletin 24(2):991.	-
	AF	Ito et al. (1982), "Polymerization of Methyul α-(Trifluoromethyl)acrylate and α- (Trifluoromethyl)Acrylonitrile and Copolymerization of These Monomers with Methyl Methacrylate," Macromolecules 15(3):915-920.	
,	AG	Ito (1984), "Radical Reactivity and Q-e Values of Methyl α-(Trifluoromethyl)acrylate," <i>Macromolecules</i> 17(10):2204-2205.	-
	AH	Ito et al. (1987), "Anionic Polymerization of α-(Trifluoromethyl)acrylate," Recent Advances in Anionic Polymerization, Elsevier, pp. 421-430.	-
	AI	Ito et al. (2001), "Novel Fluoropolymers for Use in 157 nm Lithography," Journal of Photopolymer Science and Technology 14(4):583-593.	_
1	,AJ	Ito et al. (2001), "Polymer Design for 157 nm Chmically Amplified Resists," Advances in Resist Technology and Processing XVIII, Proceedings of SPIE 4345:273-284.	
•	AK	Kunz et al. (1999), "Outlook for 157 nm Resist Design," Proceedings of SPIE 3678:13-23.	
	·AL	Schmidt et al. (1962), "Ozonisierung Cyclischer Enolather," <i>Liebigs Ann. Chem. Bd.</i> 656:97-102.	
	AM	Willson et al. (1983) "Poly (Methyl g. Trifly or grant al.	
		Willson et al. (1983), "Poly(Methyl α-Trifluoromethylacrylate) as a Positive Electron Beam Resist," Polymer Engineering and Science 23(18):1000-1003.	

Examiner		
Signature	Date	\neg
	Considered	
*EXAMINER: Initial if reference considered, whether or not situation in the		- 1

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.